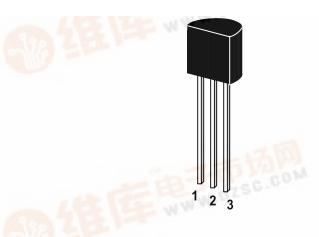
ST 2SC732 查询"2SC732"供应商

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (Ta=25°C)

E B Jun DZSC.COM	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	50	V
Emitter Base Voltage	V _{EBO}	5	COV.
Base Current	I _B	30	mA
Collector Current	l _c	150	mA
Power Dissipation	P _{tot}	400	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	Ts	-55 to +125	°C



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002

ST 2SC732 查询"2SC732"供应商

Characteristics at $T_{amb}=25$ °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V _{CE} =6V, I _C =2mA	Coin Crown G	h _{FE}	200	_	400	-
Current	Gain Group G L	h _{FE}	350	-	700	-
Base-Emitter Voltage						
at V _{CE} =6V,I _C =2mA		V_BE	-	0.65	-	V
Collector Cutoff Current						
at V _{CB} =60V		I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current						
at V _{EB} =5V		I _{EBO}	-	-	0.1	μA
Collector Saturation Voltage						
at I _C =10mA, I _B =1mA		V _{CE(sat)}	-	-	0.3	V
Gain Bandwidth Product						
at V _{CE} =6V, I _C =1mA		f⊤	-	150	-	MHz
Output Capacitance						
at V _{CB} =10V, f=1MHz		C _{OB}	-	2	-	pF
Noise Figure						
at V _{CE} =6V, I _C =0.1mA						
f=100Hz, R _G =10KΩ		NF(1)	-	0.5	6	V
Noise Figure						
at V_{CE} =6V, I _C =0.1mA						
f=1KHz, R _G =10KΩ		NF(2)	-	0.2	3	V







Dated : 07/12/2002